



Form 1449 (Modified)	Atty Docket No. NOVLP098	Application No.: 10/800,409
Information Disclosure Statement By Applicant	Applicant: Wu et al.	
(Use Several Sheets if Necessary)	Filing Date 03-11-2004	Group 1762

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
BC	A1	6,867,086 B1	03.2005	Chen et al.			
	A2	6,903,004	06.2005	Spencer et al.			
	A3	6,232,658 B1	05.2001	Catabay et al.			
	A4	6,171,661	01.2001	Zheng et al.			
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	A7	7,018,918	03.2006	Kloster et al.			
	A8	6,849,549	02.2005	Chiou et al.			
	A9	2002/0141024 A1	10.2002	Retschke et al.			
	A10	2002/0064341 A1	05.2002	Fauver et al.			
	A11	7,094,713 B1	08.22.06	Niu et al.			
	A12	6,306,564	10.2001	Mullee, William H.			
	A13	2003/0066544 A1	04.2003	Jur et al.			
	A14	6,149,828 A	11.2000	Vaartstra, Brian A.			
	A15	6,943,121 B2	09.2005	Leu et al.			
	A16	2004/0102032 A1	05.2004	Kloster et al.			
	A17	2006/0110931 A1	05.2006	Fukazawa et al.			
	A18	7,087,271 B2	08.2006	Rhee et al.			
	A19	2006/0197881	09.2006	Kang et al.			
BC	A20	6,331,480	12.2001	Tsai et al.			

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C1	U.S. Office Action mailed March 29, 2006, from U.S Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-002886].
	C2	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/941,502 [Atty Dkt No. NOVLP107/NVLS-2932].
	C3	U.S. Office Action mailed May 30, 2006, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
	C4	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
BC	C5	U.S. Office Action mailed May 2, 2006, from U.S Application No. 11/050,621 [Atty Dkt No. NOVLP100/NVLS-2956].
Examiner /Bret Chen/		Date Considered 12/01/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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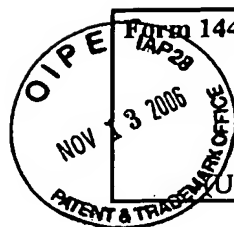
#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C6	Kelman et al., "Method for Reducing Stress in Porous Dielectric Films", U.S. Application No. 11/369,311, filed March 6, 2006 (Atty Dkt: NOVLP154/NVLS-3121)
	C7	U.S. Office Action mailed June 28, 2006, from U.S Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].
	C8	U.S. Office Action mailed May 2, 2006, from U.S Application No. 10/295,965.
	C9	U.S. Office Action mailed August 9, 2005, from U.S Application No. 10/295,965.
	C10	U.S. Office Action mailed June 14, 2006, from U.S Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919].
	C11	U.S. Office Action mailed September 8, 2006, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
	C12	U.S. Office Action mailed September 7, 2006, from U.S Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS-2889].
BC	C13	U.S. Office Action mailed July 12, 2006, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
Examiner /Bret Chen/		Date Considered 12/15/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C1	Wu et al., "Methods for Fabricating High Hardness/Modules Low Dielectric Constant Materials," Novellus Systems, Inc., Appln No. 11/369,658, filed March 6, 2006, pp. 1-33. [NOVLP148/NVLS-3111]
BC	C2	Dhas et al., "Method of Reducing Defects in PECVD TEOS Films," Novellus Systems, Inc., Appln No. 11/396,303, filed March 30, 2006, pp. 1-21. [NOVLP160/NVLS-3168]
Examiner                      /Bret Chen/		Date Considered                      12/01/2006

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